IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Rule 53(b) Divisional Application of:

Taiji EMA et al.

Divisional of S.N. 09/637,256 filed August 14, 2000 Group Art Unit: To Be Assigned

Filed: Herewith Examiner: To Be Assigned

For: SEMICONDUCTOR STORAGE DEVICE AND METHOD FOR FABRICATING THE SAME

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: March 11, 2004

Sir:

This Information Disclosure Statement is being filed in order to comply with Applicant's duty of disclosure under 37 CFR 1.56. The documents listed on the Form PTO-1449 were made of record in parent application Serial No. 09/637,256.

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,
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INFORMATION DISCLOSURE CITATION	Atty. Docket No. **960045E**	Serial No. **To be assigned**
	Applicant(s): **Taiji EMA et al.**	
	Filing Date: **Herewith**	Group Art Unit: **To be assigned**

PTO-1449

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Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AB	5,502,336	Park et al.	03/96			
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